CLAIMS

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What is claimed is:

1. An apparatus for characterizing a void in a first scan target associated with a sample, the sample having a first surface and a second surface, the apparatus comprising:

an x-ray emission inducer configured to scan a first scan target, the x-ray emission inducer causing the first scan target to emit x-rays from the first surface;

an x-ray emission detection system configured to obtain a measurement of the x-rays emitted from the first surface of the sample, wherein the x-ray measurement is compared to a control measurement to characterize a void in the first scan target.

- 2. The apparatus of claim 1, further comprising a stage configured to secure the sample, wherein the stage is configured to position the sample relative to the x-ray emission inducer.
- 3. The apparatus of claim 2, wherein positioning the sample comprises rotating the sample.
 - 4. The apparatus of claim 2, wherein the first scan target comprises a via.
- 5. The apparatus of claim 4, wherein the sample is a wafer comprising a plurality of integrated circuits.
- 6. The apparatus of claim 1, wherein the x-ray emission detection system is configured to detect x-rays with a first emission energy corresponding to a first material.
 - 7. The apparatus of claim 6, wherein the first material comprises Cu.
- 8. The apparatus of claim 7, wherein the x-ray emission detection system is further configured to detect x-rays with a second emission energy corresponding to a second material.
 - 9. The apparatus of claim 8, wherein the second material comprises Ta.
 - 10. The apparatus of claim 9, wherein the control measurement is obtained by scanning an adjacent scan target.
- 11. A system for characterizing voids associated with a sample, the sample having a first surface and a second surface, the system comprising:

memory;

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a processor coupled with memory, the processor configured to identify a first measurement of induced x-ray emissions characteristic of a first material at a first scan target, identify a control measurement, and provide the first measurement and the control measurement for comparison to thereby obtain information for characterizing a void associated with the first scan target in the sample.

- 12. The system of claim 11, wherein the first material has low resistivity.
- 13. The system of claim 12, wherein the first material is copper.
- 14. The system of claim 11, wherein the sample is a wafer comprising a plurality of integrated circuits.
- 15. The system of claim 11, further comprising identifying a second measurement of x-ray emissions characteristic of a second material.
- 16. The system of claim 11, wherein the second material is a barrier material.
 - 17. The system of claim 16, wherein the second material is Ta.
- 18. The system of claim 11, wherein characterizing voids associated with the sample comprises determining the size and location of a void.
- 19. The system of claim 11, wherein the control measurement is obtained by scanning an adjacent scan target.
 - 20. The system of claim 19, wherein the scan target is a via.
- 21. The system of claim 20, wherein the adjacent scan target is an adjacent via.
- 22. The system of claim 21, wherein the control measurement is obtained by scanning adjacent vias in the +x, -x, +y, and -y positions.
- 23. The system of claim 22, wherein the control measurement is obtained by scanning adjacent vias in the +2x, -2x, +2y, and -2y positions.
- 24. A method for characterizing a void in a sample, the method comprising: identifying a first measurement of induced x-ray emissions characteristic of a first material at a first scan target.

identifying a control measurement;

- providing the first measurement and the control measurement for comparison to thereby obtain information for characterizing a void associated with the first scan target in the sample.
- 25. The method of claim 24, wherein the first material has low resistivity.

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- 26. The method of claim 25, wherein the first material is copper.
- 27. The method of claim 24, wherein the sample is a wafer comprising a plurality of integrated circuits.
- 28. The method of claim 24, further comprising identifying a second measurement of x-ray emissions characteristic of a second material.
 - 29. The method of claim 24, wherein the second material is a barrier material.
 - 30. The method of claim 29, wherein the second material is Ta.
- The method of claim 24, wherein characterizing voids associated with the sample comprises determining the size and location of a void.
 - 32. The method of claim 24, wherein the control measurement is obtained by scanning an adjacent scan target.
 - 33. The method of claim 32, wherein the scan target is a via.
 - 34. The method of claim 33, wherein the adjacent scan target is an adjacent via.
 - 35. The method of claim 34, wherein the control measurement is obtained by scanning adjacent vias in the +x, -x, +y, and -y positions.
 - 36. The method of claim 35, wherein the control measurement is obtained by scanning adjacent vias in the +2x, -2x, +2y, and -2y positions.
 - 37. An apparatus for characterizing a void in a sample, the apparatus comprising:

means for identifying a first measurement of induced x-ray emissions characteristic of a first material at a first scan target.

means for identifying a control measurement;

means for providing the first measurement and the control measurement for comparison to thereby obtain information for characterizing a void associated with the first scan target in the sample.

- 38. The apparatus of claim 37, wherein the control measurement is obtained by scanning an adjacent scan target.
- 39. The apparatus of claim 38, wherein the adjacent scan target is an adjacent via.
- 40. The apparatus of claim 39, wherein the control measurement is obtained by scanning adjacent vias in the +x, -x, +y, and -y positions.

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41. The apparatus of claim 40, wherein the control measurement is obtained by scanning adjacent vias in the +2x, -2x, +2y, and -2y positions.